



RF Power GaN Transistor

This 125 W RF power GaN transistor is capable of broadband operation from 30 to 2200 MHz and includes input matching for extended bandwidth performance. With its high gain and high ruggedness, this device is ideally suited for CW, pulse and broadband RF applications.

This part is characterized and performance is guaranteed for applications operating in the 30 to 2200 MHz band. There is no guarantee of performance when this part is used in applications designed outside of these frequencies.

Typical Performance: $V_{DD} = 50 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

Frequency (MHz)	Signal Type	P_{out} (W)	G_{ps} (dB)	η_D (%)
30–940 (1,2)	CW	90	16.0	45.0
520 (1)	CW	125	18.0	59.1
940 (1)	CW	80	18.4	44.0
2200	Pulse (100 μsec , 20% Duty Cycle)	200	17.0	57.0

Load Mismatch/Ruggedness

Frequency (MHz)	Signal Type	VSWR	P_{in} (W)	Test Voltage	Result
520 (1)	Pulse (100 μsec , 20% Duty Cycle)	> 10:1 at All Phase Angles	3.4 (3 dB Overdrive)	50	No Device Degradation

1. Measured in 30–940 MHz wideband reference circuit (page 4).
2. The values shown are the minimum measured efficiency performance numbers across the indicated frequency range.

Features

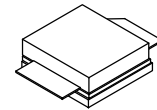
- Advanced GaN on SiC, offering high power density
- Decade bandwidth performance
- Input matched for extended wideband performance
- High ruggedness: > 10:1 VSWR

Typical Applications

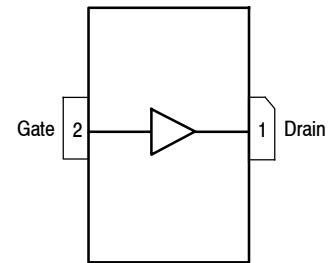
- Ideal for military end-use applications, including the following:
 - Narrowband and multi-octave wideband amplifiers
 - Radar
 - Jammers
 - EMC testing
- Also suitable for commercial applications, including the following:
 - Public mobile radios, including emergency service radios
 - Industrial, scientific and medical
 - Wideband laboratory amplifiers
 - Wireless cellular infrastructure

MMRF5017HS

**30–2200 MHz, 125 W CW, 50 V
 WIDEBAND
 RF POWER GaN TRANSISTOR**



NI-400S-2S



(Top View)

Note: The backside of the package is the source terminal for the transistor.

Figure 1. Pin Connections



Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	125	Vdc
Gate-Source Voltage	V_{GS}	-8, 0	Vdc
Operating Voltage	V_{DD}	0 to +55	Vdc
Maximum Forward Gate Current @ $T_C = 25^\circ\text{C}$	I_{GMAX}	24	mA
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Case Operating Temperature Range	T_C	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +225	$^\circ\text{C}$
Absolute Maximum Channel Temperature (1)	T_{MAX}	350	$^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	154 0.77	W W/ $^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic (2)	Symbol	Value	Unit
Thermal Resistance by Infrared Measurement, Active Die Surface-to-Case CW: Case Temperature 81°C , 80 W CW, 50 Vdc, $I_{DQ} = 200$ mA, 940 MHz	$R_{\theta JC}$ (IR)	1.3 (3)	$^\circ\text{C}/\text{W}$
Thermal Resistance by Finite Element Analysis, Channel-to-Case Case Temperature 90°C , $P_D = 96$ W	$R_{\theta CHC}$ (FEA)	1.77 (4)	$^\circ\text{C}/\text{W}$

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JS-001-2017)	2, passes 2500 V
Charge Device Model (per JS-002-2014)	II, passes 200 V

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage ($V_{GS} = -8$ Vdc, $I_D = 20$ mAdc)	$V_{(BR)DSS}$	150	—	—	Vdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10$ Vdc, $I_D = 20$ mAdc)	$V_{GS(th)}$	-3.8	-3.0	-2.3	Vdc
Gate Quiescent Voltage ($V_{DD} = 48$ Vdc, $I_D = 200$ mAdc, Measured in Functional Test)	$V_{GS(Q)}$	-3.6	-3.1	-2.3	Vdc
Gate-Source Leakage Current ($V_{DS} = 0$ Vdc, $V_{GS} = -5$ Vdc)	I_{GSS}	-7.5	—	—	mAdc

Table 5. Ordering Information

Device	Tape and Reel Information	Package
MMRF5017HSR5	R5 Suffix = 50 Units, 32 mm Tape Width, 13-inch Reel	NI-400S-2S

- Reliability tests were conducted at 225°C . Operation with T_{MAX} at 350°C will reduce median time to failure.
- Characterized in 30–940 MHz reference circuit at 940 MHz and 80 W CW output power.
- Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.nxp.com/RF> and search for AN1955.
- $R_{\theta CHC}$ (FEA) must be used for purposes related to reliability and limitations on maximum channel temperature. MTTF may be estimated by the expression $MTTF$ (hours) = $10^{[A + B/(T + 273)]}$, where T is the channel temperature in degrees Celsius, $A = -10.3$ and $B = 8260$.

NOTE: Correct Biasing Sequence for GaN Depletion Mode Transistors

Turning the device ON

1. Set V_{GS} to -5 V
2. Turn on V_{DS} to nominal supply voltage (50 V)
3. Increase V_{GS} until I_{DS} current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce V_{GS} down to -5 V
3. Reduce V_{DS} down to 0 V (Adequate time must be allowed for V_{DS} to reduce to 0 V to prevent severe damage to device.)
4. Turn off V_{GS}

30–940 MHz WIDEBAND REFERENCE CIRCUIT — 2.0" x 5.0" (5.1 cm x 12.7 cm)

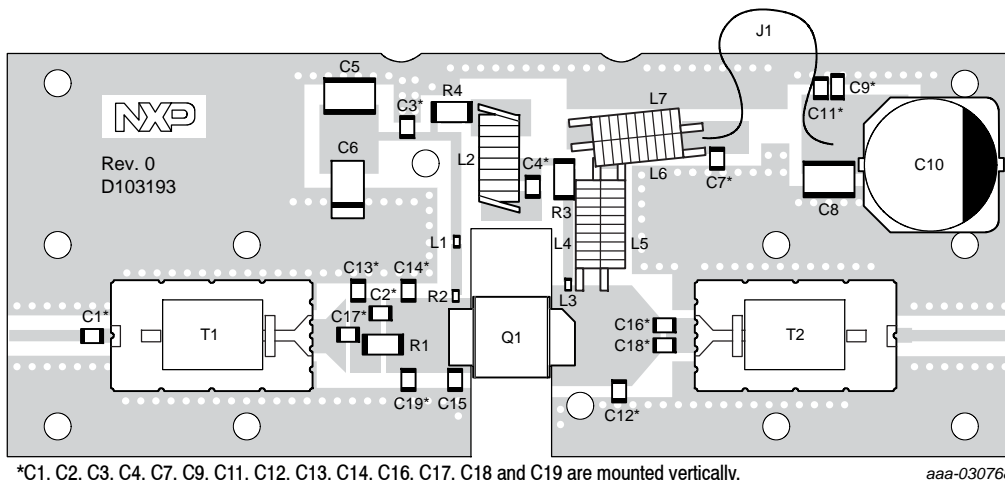


Figure 2. MMRF5017HS Wideband Reference Circuit Component Layout — 30–940 MHz

Table 6. MMRF5017HS Wideband Reference Circuit Component Designations and Values — 30–940 MHz

Part	Description	Part Number	Manufacturer
C1	1500 pF Chip Capacitor	ATC700B152JT50XT	ATC
C2	100 pF Chip Capacitor	ATC800B101JT500XT	ATC
C3, C7	39 pF Chip Capacitor	ATC800B390JT500XT	ATC
C4	680 pF Chip Capacitor	ATC800B681JT50XT	ATC
C5, C8	2.2 μ F Chip Capacitor	C3225X7R2A225KT	TDK
C6	22 μ F, 25 V Tantalum Capacitor	TPSD226M025R0200	AVX
C9	0.1 μ F Chip Capacitor	C1206C104K1RACTU	Kemet
C10	220 μ F, 100 V Electrolytic Capacitor	EEV-FK2A221M	Panasonic-ECG
C11	220 pF Chip Capacitor	ATC100B221JT200XT	ATC
C12	2.2 pF Chip Capacitor	ATC800B2R2BT500XT	ATC
C13, C14, C19	5.6 pF Chip Capacitor	ATC800B5R6CT500XT	ATC
C15	10 pF Chip Capacitor	ATC800B100JT500XT	ATC
C16, C18	470 pF Chip Capacitor	ATC800B471JT200XT	ATC
C17	330 pF Chip Capacitor	ATC800B331JT200XT	ATC
J1	#16 AWG, Magnetic Wire, Length = 2.5"	8074	Belden
L1	270 nH Inductor	0603AF-271XJRU	Coilcraft
L2	422 nH inductor	132-18SMJL	Coilcraft
L3	240 nH Inductor	0603AF-241XJRU	Coilcraft
L4, L5, L6, L7	1.3 μ H Inductor	4310LC-132KE	Coilcraft
Q1	RF Power GaN Transistor	MMRF5017HS	NXP
R1	51 Ω , 1/2 W Chip Resistor	CRCW201051R0JNEF	Vishay
R2	10 Ω , 1/4 W Chip Resistor	CRCW080510R0FKEA	Vishay
R3, R4	100 Ω , 4 W Chip Resistor	CW12010T0100GBK	ATC
T1, T2	High Power Transformer, 30–1000 MHz, 50 Ω to 12.5 Ω	XMT0310B5012	Anaren
PCB	Shengyi S1000-2, 0.031", $\epsilon_r = 4.8$	D103193	MTL

TYPICAL CHARACTERISTICS — 30–940 MHz WIDEBAND REFERENCE CIRCUIT

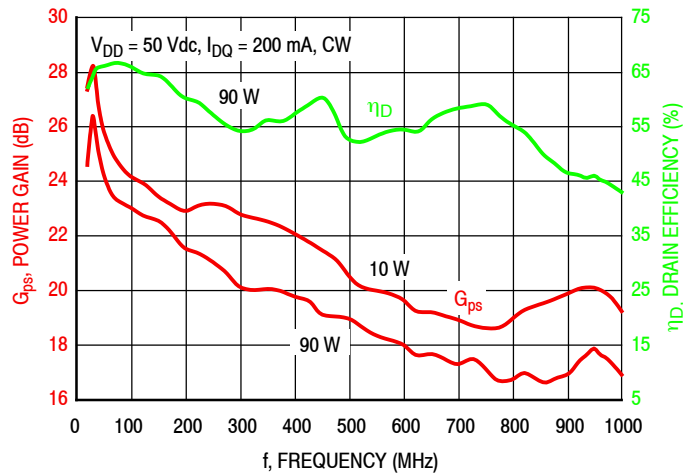


Figure 3. Power Gain and Drain Efficiency versus Output Power and Frequency

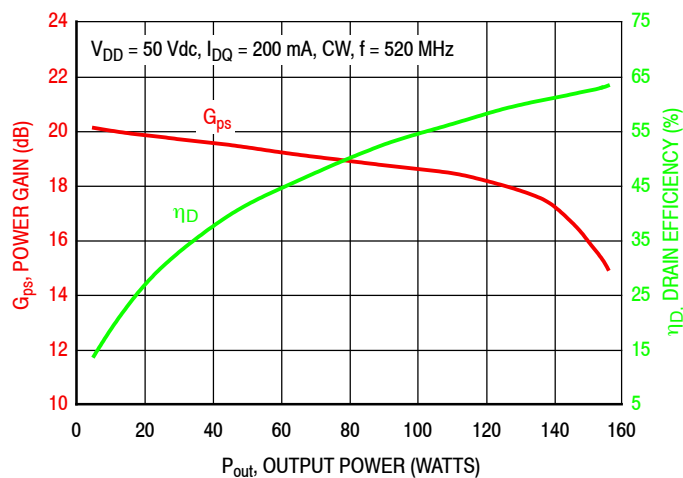


Figure 4. Power Gain and Drain Efficiency versus CW Output Power – 520 MHz

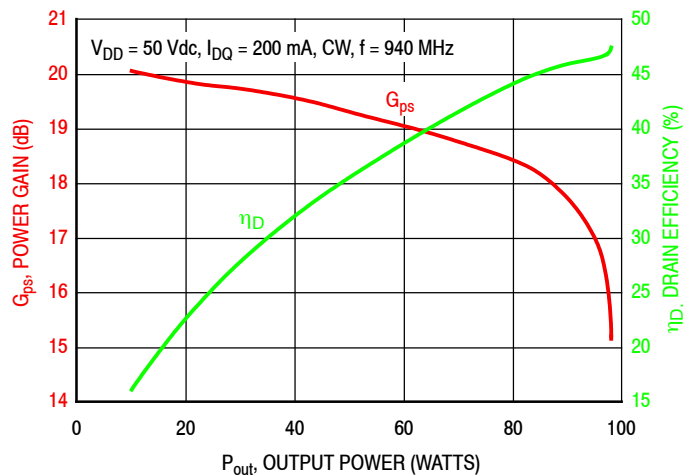


Figure 5. Power Gain and Drain Efficiency versus CW Output Power – 940 MHz

30–940 MHz WIDEBAND REFERENCE CIRCUIT

f MHz	Z _{source} Ω	Z _{load} Ω
20	39.0 + j23.1	11.3 – j5.0
30	59.6 – j3.7	11.0 – j3.1
50	28.3 – j28.7	11.1 – j1.8
70	15.5 – j22.2	11.2 – j1.3
90	11.1 – j17.3	11.3 – j1.1
136	7.9 – j11.3	10.7 – j1.4
174	7.0 – j8.9	10.0 – j0.3
360	6.2 – j5.0	11.9 – j0.2
440	6.0 – j4.6	11.9 – j0.0
520	5.5 – j4.7	12.3 – j0.1
760	2.5 – j4.0	14.4 – j1.2
850	1.7 – j2.9	16.2 – j3.5
940	1.1 – j1.8	15.9 – j7.9
1000	1.0 – j1.1	13.2 – j10.6

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

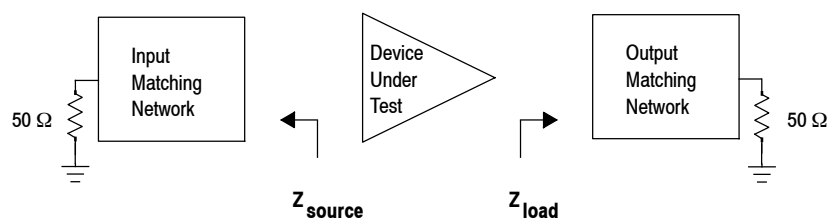
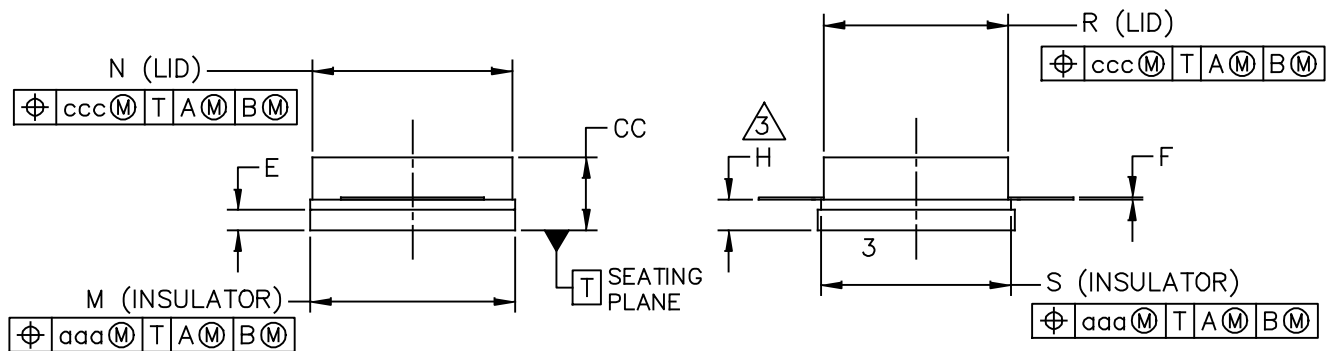
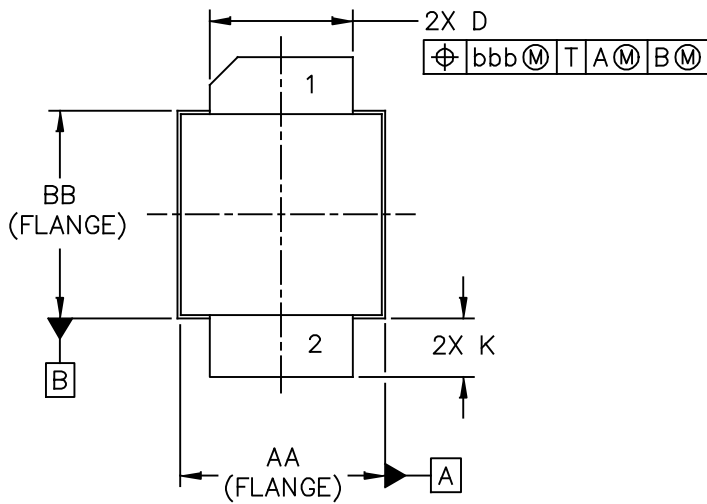


Figure 6. Wideband Series Equivalent Source and Load Impedance — 30–940 MHz

PACKAGE DIMENSIONS



© NXP SEMICONDUCTORS N.V. ALL RIGHTS RESERVED	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE						
TITLE: <div style="text-align: center; font-size: 1.2em;">NI-400S-2S</div>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 60%;">DOCUMENT NO: 98ASA10732D</td> <td style="width: 40%;">REV: C</td> </tr> <tr> <td colspan="2">STANDARD: NON-JEDEC</td> </tr> <tr> <td>SOT1828-1</td> <td style="text-align: right;">13 JAN 2016</td> </tr> </table>		DOCUMENT NO: 98ASA10732D	REV: C	STANDARD: NON-JEDEC		SOT1828-1	13 JAN 2016
DOCUMENT NO: 98ASA10732D	REV: C							
STANDARD: NON-JEDEC								
SOT1828-1	13 JAN 2016							

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.

③ DIMENSION H IS MEASURED .030 INCH (0.762 MM) AWAY FROM THE FLANGE TO CLEAR THE EPOXY FLOW OUT REGION PARALLEL TO DATUM B.

4. INPUT & OUTPUT LEADS (PIN 1 & 2) MAY HAVE SMALL FEATURES SUCH AS SQUARE HOLES OR NOTCHES FOR MANUFACTURING CONVENIENCE.

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
AA	.395	.405	10.03	10.29	aaa	.005			0.13
BB	.382	.388	9.70	9.86	bbb	.010			0.25
CC	.125	.163	3.18	4.14	ccc	.015			0.38
D	.275	.285	6.98	7.24					
E	.035	.045	0.89	1.14					
F	.004	.006	0.10	0.15					
H	.057	.067	1.45	1.70					
K	.0995	.1295	2.53	3.29					
M	.395	.405	10.03	10.29					
N	.385	.395	9.78	10.03					
R	.355	.365	9.02	9.27					
S	.365	.375	9.27	9.53					
© NXP SEMICONDUCTORS N.V. ALL RIGHTS RESERVED			MECHANICAL OUTLINE			PRINT VERSION NOT TO SCALE			
TITLE: NI-400S-2S					DOCUMENT NO: 98ASA10732D			REV: C	
					STANDARD: NON-JEDEC				
					SOT1828-1			13 JAN 2016	

PRODUCT DOCUMENTATION AND TOOLS

Refer to the following resources to aid your design process.

Application Notes

- AN1908: Solder Reflow Attach Method for High Power RF Devices in Air Cavity Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Development Tools

- Printed Circuit Boards

To Download Resources Specific to a Given Part Number:

1. Go to <http://www.nxp.com/RF>
2. Search by part number
3. Click part number link
4. Choose the desired resource from the drop down menu

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	June 2018	• Initial release of data sheet

How to Reach Us:

Home Page:
nxp.com

Web Support:
nxp.com/support

Information in this document is provided solely to enable system and software implementers to use NXP products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits based on the information in this document. NXP reserves the right to make changes without further notice to any products herein.

NXP makes no warranty, representation, or guarantee regarding the suitability of its products for any particular purpose, nor does NXP assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters that may be provided in NXP data sheets and/or specifications can and do vary in different applications, and actual performance may vary over time. All operating parameters, including "typicals," must be validated for each customer application by customer's technical experts. NXP does not convey any license under its patent rights nor the rights of others. NXP sells products pursuant to standard terms and conditions of sale, which can be found at the following address: nxp.com/SalesTermsandConditions.

NXP and the NXP logo are trademarks of NXP B.V. All other product or service names are the property of their respective owners.

© 2018 NXP B.V.





Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.